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Attorney's Docket No.: 07977-093002 / US3164D1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Hisashi Ohtani, et al. Art Unit : 2815  
Serial No.: 09/379,702 Examiner : Eugene Lee  
Filed : August 24, 1999  
Title : METHOD OF FABRICATING SEMICONDUCTOR DEVICES

Commissioner for Patents  
Washington, D.C. 20231

RESPONSE

In response to the action mailed February 14, 2002, please  
amend the application as follows:

In the claims:

Please cancel all pending claims, specifically claims  
2-12, 14-25, 27, 28, and 30-44.

Please substitute new claims 45-64 as follows:

*sub G1*  
*E,*

--45. A semiconductor device comprising:  
a crystalline semiconductor island comprising silicon  
over  
a substrate, the crystalline semiconductor island  
comprising a source region, a drain region and a channel  
formation region provided between the source and the drain  
region; and

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